

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 1, line 14, as follows:

Conventionally, mainly in a field of [[the]] semiconductor manufacturing, etching processing of a fine pattern on a surface of a substrate such as a silicon wafer and formation of various kinds of functional thin films such as an oxide thin film and a nitride film by surface reforming, plasma chemical deposition or sputtering have been performed extremely accurately by the use of the plasma process.

Please amend the paragraph beginning at page 1, line 20, as follows:

However, the particulate dust containing clusters generated in the reactive plasma vapor phase has deposited not only on the substrate surface but also on an inner wall surface of the high vacuum enclosure being a reaction enclosure to contaminate the inside of the high vacuum enclosure. Not only the particulates but also particulates flown into plasma due to peeling of a deposition film deposited in this manner are negatively electrified in plasma, electrically trapped by a plasma boundary region on a substrate front surface to flow onto the substrate surface, and thus deteriorating processing accuracy and [[a]] film quality, which has been a serious problem.

Please amend the paragraph beginning at page 2, line 15, as follows:

(4) The substrate is arranged to face downward or [[side]] sideward to prevent the particulates from falling onto the substrate, and the number of mobile portions is made as small as possible to prevent generation of the particulates due to peeling.

Please amend the paragraph beginning at page 3, line 18, as follows:

To solve the foregoing problems, the processing method of the particulate dust in plasma of the present invention is one in which the particulate dust in plasma is processed when a

substrate to be processed is arranged in ~~[[the]]~~ a high vacuum enclosure, plasma is generated in the high vacuum enclosure, and a reactive material is appropriately introduced into the high vacuum enclosure to perform processing of the substrate to be processed, wherein at least one collecting electrode is provided around the substrate to be processed in the high vacuum enclosure other than an electrode performing the generation of plasma, and a predetermined electric potential of direct current or alternating current is appropriately applied to the collecting electrode.

Please amend the paragraph beginning at page 4, line 26, as follows:

In the processing apparatus of the particulate dust in plasma of the present invention, it is preferable that the collecting electrode has a structure that includes: a storage space for storing the particulates collected therein; and an opening communicating between the storage space and the inside of the high vacuum enclosure.

Please amend the paragraph beginning at page 5, line 15, as follows:

Accordingly, since ~~[[the]]~~ a particulate drawing electrode is provided, the generated particulates that is negatively electrified can be efficiently drawn out from plasma and the amount of the particulates absorbed into the storage space from the opening can be increased.

HAYES SOLOWAY P.C.
130 W. CUSHING ST.
TUCSON, AZ 85701
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567